


Visualizing Electrical Breakdown and ON/OFF States in Electrically Switchable Suspended Graphene Break Junctions

Hang Zhang,^{†,§} Wenzhong Bao,^{†,§} Zeng Zhao,[†] Jhao-Wun Huang,[†] Brian Standley,[‡] Gang Liu,[†] Fenglin Wang,[†] Philip Kratz,[†] Lei Jing,[†] Marc Bockrath,^{*,†,‡} and Chun Ning Lau^{*,†}

[†]Department of Physics and Astronomy, University of California, Riverside, California 92521, United States

[‡]Department of Applied Physics, California Institute of Technology, Pasadena, California 91125, United States

 *Supporting Information*

Zoltán Scherübl

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BUTE

Sample

Si/SiO₂ (300 nm) substrate

1-5 layer graphene (mechanical exfoliation)

2 methods:

- EBL and 120 nm oxide etching
- Exfoliation on prepatterned substrate (250 nm deep)
 - 10/70 nm Ti/Au with shadow mask

$G_{2p} \sim 0.5 \text{ mS}$

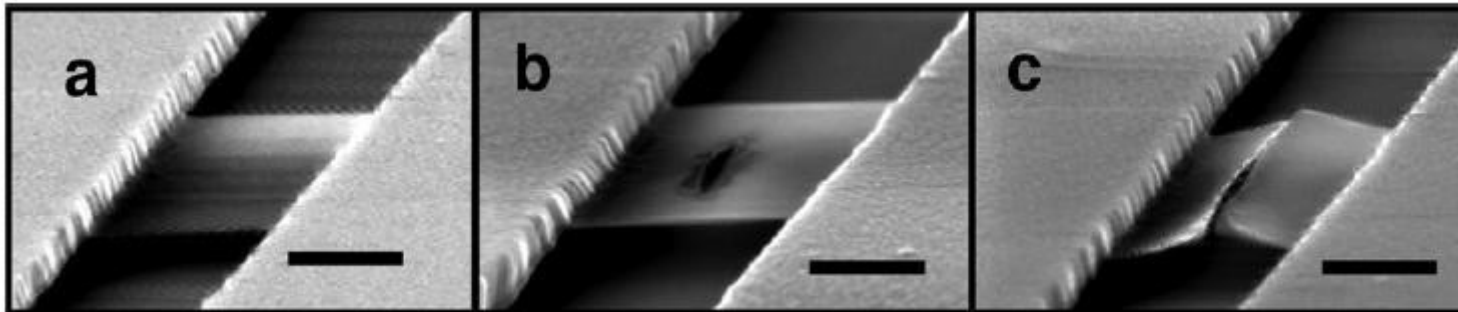
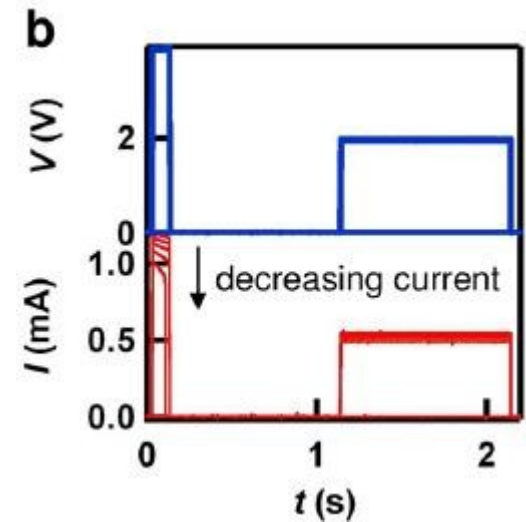
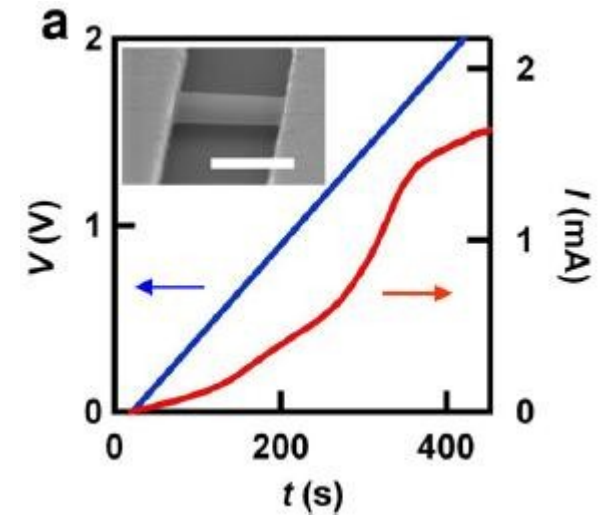
Electromigration (in situ SEM vid):

High vacuum: 10^{-6} Torr

$\sim 4 \text{ V pulse} \rightarrow \sim 2 \text{ mA}/\mu\text{m}$

$\sim 2 \text{ V test voltage}$

Start: center/edge (depend on T, defects etc.)



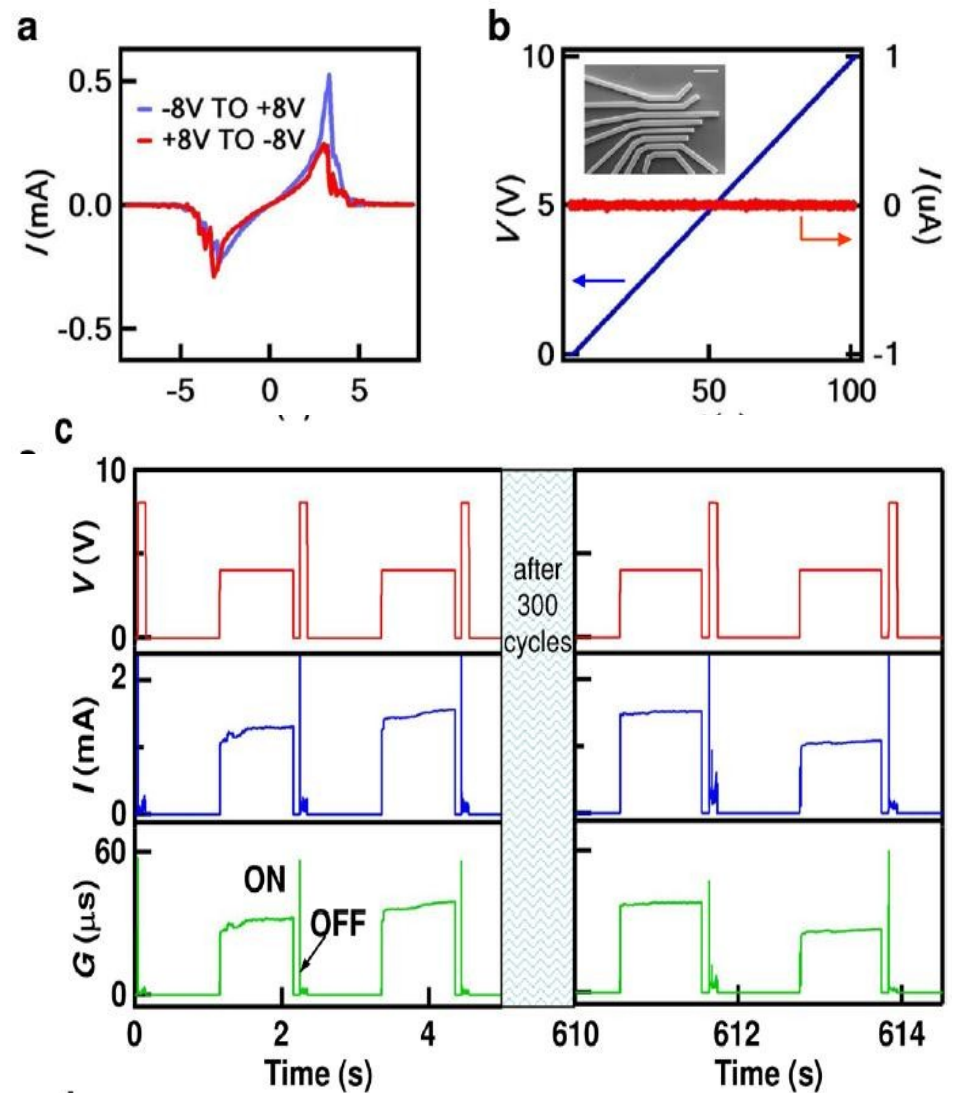
Switch

UHV needed (clean sample)
Atomic motion
Chemical rearrangement
Both

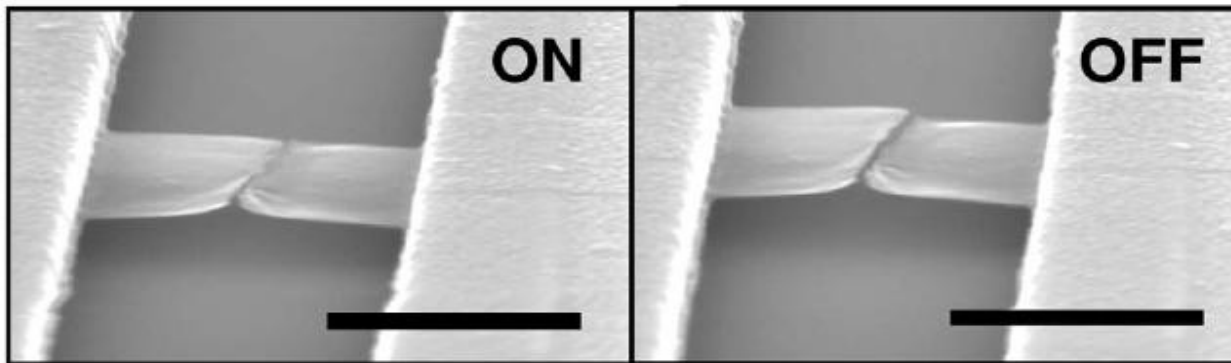
Open @ $\pm 4V$ ('ON') 25-40 μS
Close (8V pulse) ('OFF') $\sim 1\mu S$
Hundreds of cycles

Less cycle before failure than
@ nonsuspended samples

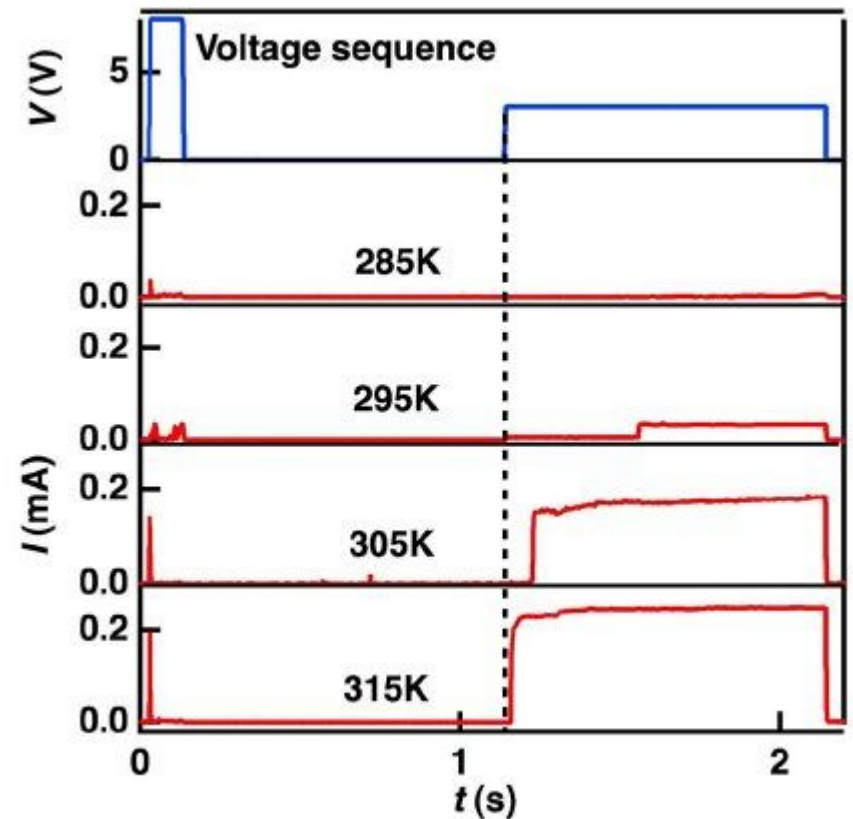
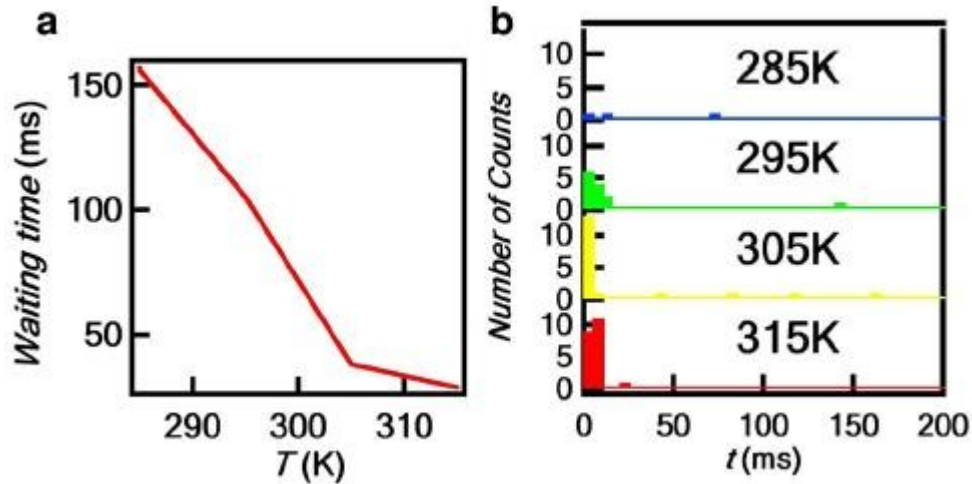
Control device: w/o graphene
Almost zero current @ 10V
Breakdown @ 210 V



d



Temperature dependence



No switching @4.5K

Very rare under 280 K

Estimated max freq: ~ 1 MHz
(graphene cantilever)

Another time scale ~ 1 ms

Measured timescale: ~ 100 ms – 1s $\gg 1$ ms

Elastic properties: weak T dependence

Switching not limited by nanomechanical motion, but atomic motion/
chemical rearrangements (\sim eV energy scale)